



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

4.0 A

Features

- R_{DS(ON)}, V_{GS}@10V,I_D@3.0A<100mΩ
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@2.0A<110m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

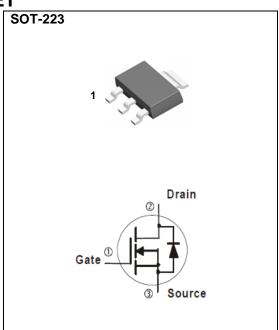
Mechanical Data

• Case: SOT-223 Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.043 ounces, 0.123 grams

Marking: W4N06A



Maximum Ratings and Thermal Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _A =25°C	I _D	4	А	
	T _A =70°C		3.2		
Pulsed Drain Current (Note 1)		I _{DM}	8	А	
Power Dissipation	T _A =25°C	P _D	3.1		
	T _A =70°C		2	W	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal resistance - Junction to Ambient (Note 5)		$R_{\theta JA}$	40.3	°C/W	

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.86	2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =3.0A	-	85	100	mΩ
		V _{GS} =4.5V,I _D =2.0A	-	95	110	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =48V, V_{GS} =0V	-	-	1.0	uA
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	V _{DS} =48V, I _D =3A, V _{GS} =4.5V ^(Note 2,3)	-	5.1	-	nC
Gate-Source Charge	Q_{gs}		-	1.2	-	
Gate-Drain Charge	Q_{gd}		-	1.9	-	
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V,	-	509	-	pF
Output Capacitance	Coss		-	39	-	
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	26	-	
Turn-On Delay Time	td _(on)	\/ 00\/ I 0A	-	1.6	-	ns
Turn-On Rise Time	t _r	V_{DD} =30V, I_{D} =3A, V_{GS} =10V, R_{G} =3.3 Ω (Note 2,3)	-	7.3	-	
Turn-Off Delay Time	td _(off)		-	25	-	
Turn-Off Fall Time	t _f	K _G =3.312	-	14	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	_		-	-	4	А
Diode Forward Current	I _S					
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.8	1.2	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

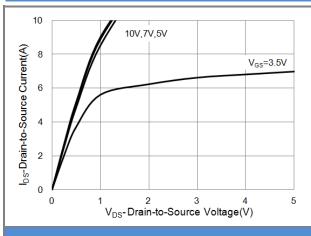


Fig.1 Output Characteristics

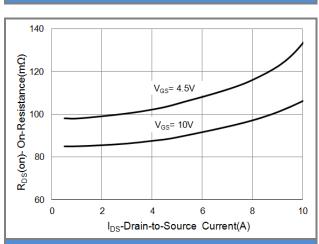


Fig.3 On-Resistance vs. Drain Current

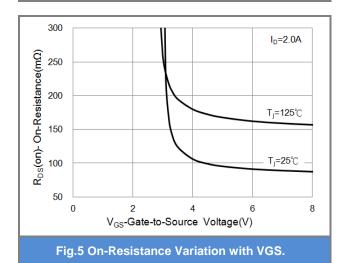


Fig.2 Transfer Characteristics

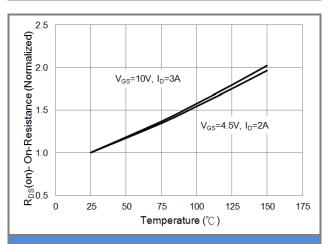


Fig.4 On-Resistance vs. Junction temperature

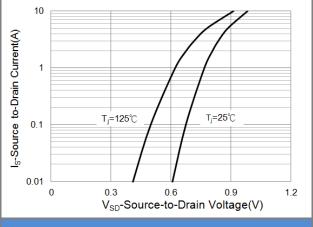


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

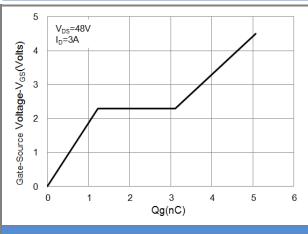


Fig.7 Gate-Charge Characteristics

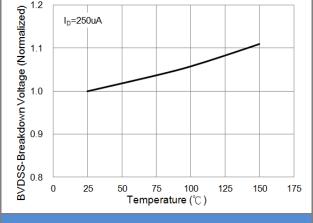


Fig.8 Breakdown Voltage Variation vs. Temperature

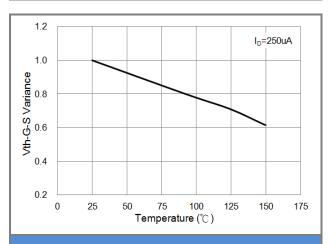


Fig.9 Threshold Voltage Variation with Temperature

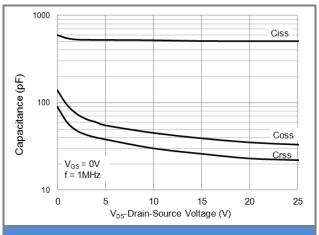
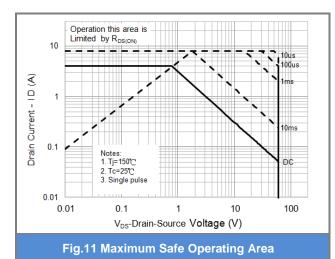


Fig.10 Capacitance vs. Drain-Source Voltage



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TYPICAL CHARACTERISTIC CURVES

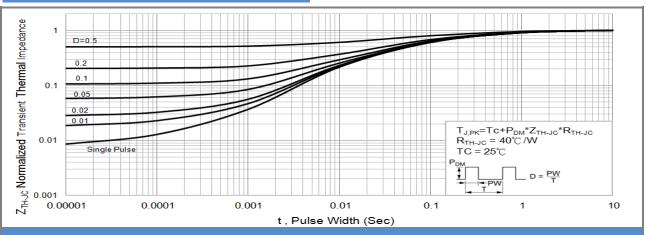
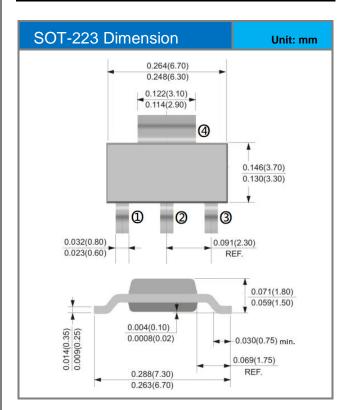


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





Packaging Information



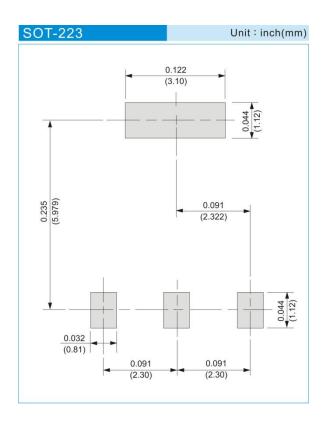




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version	
PJW4N06A_R2_00001	SOT-223	2,500pcs / 13" reel	W4N06A	Halogen free	

MOUNTING PAD LAYOUT



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